L Number	Hits	Search Text	DB	Time stamp
-	71	356/$.ccls. and (gate adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/02 14:04
-	59	356/$.ccls. and (gate adj oxide)	USPAT	2003/07/02 14:05
-	5	(gate adj oxide) and thickness and (high$1k) and scatter$	USPAT	2003/07/02 15:19
-	55	356/$.ccls. and (gate adj oxide) and thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/02 15:25
-	231	(halliyal-arvind singh-bhanwar subramanian-ramkumar).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/02 15:26
-	18	(halliyal-arvind singh-bhanwar subramanian-ramkumar).in. and (gate adj oxide) and thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/02 15:26
-	22	356/$.ccls. and (gate adj oxide) and (thickness or uniform$) and scatter$	USPAT	2003/07/08 14:44
-	28	356/$.ccls. and (gate adj oxide) and (thickness or uniform$) and scatter$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/08 16:56
-	9	("4710030" | "4750822" | "5298970" | "5608526" | "5798837" | "5978074" | "6060374" | "6081330" | "6381009").PN.	USPAT	2003/07/08 16:28
-	5	("4710030" | "4750822" | "5298970" | "5608526" | "5798837" | "5978074" | "6060374" | "6081330" | "6381009").PN. and scatter$	USPAT	2003/07/08 16:29
-	0	("4710030" | "4750822" | "5298970" | "5608526" | "5798837" | "5978074" | "6060374" | "6081330" | "6381009").PN. and scatter$ and (gate adj oxide)	USPAT	2003/07/08 16:29
-	32	250/$.ccls. and (gate adj oxide) and (thickness or uniform$) and scatter$	USPAT	2003/07/08 16:30
-	30	250/$.ccls. and (gate adj oxide) and (thickness or uniform$) and scatter$ not 356/$.ccls.	USPAT	2003/07/08 16:30
-	33	250/$.ccls. and (gate adj oxide) and (thickness or uniform$) and scatter$ not 356/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/08 16:45
-	622	((gate adj oxide) with (thickness or uniform$)) and scatter$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/09 12:10
-	19	((gate adj oxide) with (thickness or uniform$)) and scatter$.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/08 16:46
-	2	356/630-632.ccls. and (gate adj oxide) and scatter$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/09 16:26
-	14	((gate adj oxide) with (thickness or uniform$)).ab. and scatter$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/09 12:38

–	0	("5862054" "6060374" "5880040").pn. and scatter$	USPAT	2003/07/09 12:37
–	3	("5862054" "6060374" "5880040").pn.	USPAT	2003/07/09 15:11
–	9452	(438/263,786,514,14-18,769 257/e21.193,e29.162 700/121,108,109 702/181).ccls. ((gate adj oxide) with (thickness or uniform$)) and scatter$ and (nitrid$ or nitrogen$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/09 12:41
–	9035	(438/263,786,514,14-18,769 257/e21.193,e29.162 700/121,108,109 702/181).ccls. ((gate adj oxide) with (thickness or uniform$)) and scatter$.ab. and (nitrid$ or nitrogen$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/09 12:41
–	4	(438/263,786,514,14-18,769 257/e21.193,e29.162 700/121,108,109 702/181).ccls. and ((gate adj oxide) with (thickness or uniform$)) and scatter$.ab. and (nitrid$ or nitrogen$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/09 12:44
–	1	(438/263,786,514,14-18,769 257/e21.193,e29.162 700/121,108,109 702/181).ccls. and ((gate adj oxide) with (thickness or uniform$)).ab. and scatter$ and (nitrid$ or nitrogen$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/09 12:45
–	31	(438/263,786,514,14-18,769 257/e21.193,e29.162 700/121,108,109 702/181).ccls. and ((gate adj oxide) with (thickness or uniform$)) and scatter$ and (nitrid$ or nitrogen$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/10 15:43
–	3	("6528433" "5904523" "6060374").pn.	USPAT	2003/07/09 15:12
–	2	("20020023900" "20030042432").pn.	US-PGPUB	2003/07/09 15:13
–	116	356/630-632.ccls. and (semiconductor or wafer) and scatter$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/09 16:26
–	10	356/630-632.ccls. and (semiconductor or wafer) and scatter$.ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/10 11:43
–	1	356/630-632.ccls. and (semiconductor or wafer) and (scatterometry with thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/09 16:36
–	0	(scatterometry with nitrogen) and (semiconductor or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/09 16:36
–	0	(scatterometry with nitrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/09 16:36
–	679	(scatter$ with nitrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/09 16:36
–	195	(scatter$ with nitrogen) and (semiconductor or wafer or (gate adj oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/09 16:37
–	55	(scatter$ with nitrogen) and (semiconductor or wafer or (gate adj oxide)) and scatter$.ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/09 16:39

–	47	(scatter$ with nitrogen) and (semiconductor or wafer or (gate adj oxide)) and scatter$.ab. not (electron near4 beam)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/09 16:40
–	26	(scatter$ with nitrogen) and (semiconductor or wafer or (gate adj oxide)) and (scatter$ and (nitrogen or nitride$)).ab. not (electron near4 beam)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/09 16:40
–	9	("5867276" | "5877880" | "5880838" | "6051348" | "6081334" | "6141107" | "6245584" | "6383888" | "6423977").PN.	USPAT	2003/07/10 11:16
–	1	("5867276" | "5877880" | "5880838" | "6051348" | "6081334" | "6141107" | "6245584" | "6383888" | "6423977").PN. and scatter$.ab.	USPAT	2003/07/10 11:18
–	4	("4710642" | "5164790" | "5241369" | "5703692").PN.	USPAT	2003/07/10 11:17
–	4	("5867276" | "5877880" | "5880838" | "6051348" | "6081334" | "6141107" | "6245584" | "6383888" | "6423977").PN. and scatteromet$	USPAT	2003/07/10 11:18
–	17	356/630-632.ccls. and (semiconductor or wafer) and scatterom$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/10 12:01
–	16	356/630-632.ccls. and (semiconductor or wafer) and scatterom$ not scatter$.ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/10 11:43
–	6	356/237.4,237.5.ccls. and (semiconductor or wafer) and scatterom$ and thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/10 14:17
–	7	250/559.27.ccls. and (semiconductor or wafer) and scatterom$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/10 11:55
–	1	250/559.27.ccls. and (semiconductor or wafer) and scatterom$	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/07/10 11:55
–	21	356/630-632.ccls. and scatterom$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/10 12:01
–	10	356/630-632.ccls. and scatterom$	USPAT	2003/07/10 12:01
–	154	356/630-632.ccls. and scatter$	USPAT	2003/07/10 12:01
–	20	356/630-632.ccls. and scatter$.ab.	USPAT	2003/07/10 12:02
–	20	356/630-632.ccls. and scatter$.ab. and scatter$	USPAT	2003/07/10 12:02
–	35	356/$.ccls. and (semiconductor or wafer) and scatterom$.ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/10 14:17
–	8	("5393624" | "5867276" | "5923423" | "6100985" | "6259521" | "6266125" | "6388253" | "6424417").PN.	USPAT	2003/07/10 15:27
–	2	("5393624" | "5867276" | "5923423" | "6100985" | "6259521" | "6266125" | "6388253" | "6424417").PN. and (nitrogen$ or nitride$)	USPAT	2003/07/10 15:27

| - | 61 | (438/263,786,514,14-18,769 257/e21.193,e29.162 700/121,108,109 702/181).ccls. and ((gate adj oxide) with cvd) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/07/10 15:54 |
| - | 19 | (438/263,786,514,14-18,769 257/e21.193,e29.162 700/121,108,109 702/181).ccls. and (gate adj oxide).ab. and ((gate adj oxide) with cvd) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/07/10 15:57 |